

isc Silicon PNP Power Transistor

DESCRIPTION

- Standard TO–220 Package
- Gain Range of 50 200 at 500 mAdc/10 volts
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

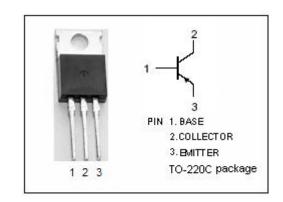
 Designed forvertical output of 14-inch to 17-inch televisions and CRT monitors, as well as other applications requiring a 150 volt PNP transistor.

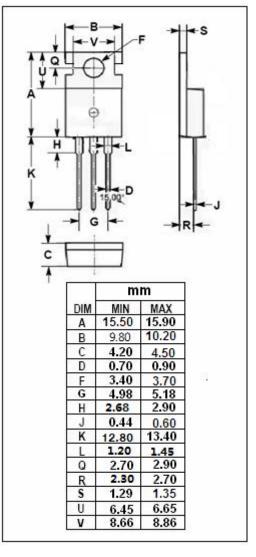
ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|------------|
| V _{CBO} | Collector-Base Voltage | -200 | V |
| V _{CEO} | Collector-Emitter Voltage | -150 | V |
| V _{EBO} | Emitter-Base Voltage | -6 | V |
| Ic | Collector Current-Continuous | -3 | А |
| I _{CM} | Collector Current-Peak | -5 | А |
| Pc | Total Power Dissipation @ T _C =25°C | 40 | W |
| TJ | Junction Temperature | 150 | $^{\circ}$ |
| T _{stg} | Storage Temperature Range | -55~150 | $^{\circ}$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT | |
|---------------------|-------------------------------------|------|------|--|
| R _{th j-c} | Thermal Resistance,Junction to Case | 3.12 | °C/W | |







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MJE9780

ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|------|------|------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = -50mA ; I _B = 0 | -150 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = -5mA ; I _C = 0 | -6 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -0.5A; I _B = -50mA | | | -0.8 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = -0.5A ; V _{CE} = -4V | | | -1.5 | V |
| Ісво | Collector Cutoff Current | V _{CB} = -150V ; I _E = 0 | | | -10 | μА |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -5V; I _C = 0 | | | -10 | μА |
| h _{FE 1} | DC Current Gain | I _C = -0.5A; V _{CE} = -10V | 50 | | 200 | |
| h _{FE 2} | DC Current Gain | Ic= -0.05A ; VcE= -10V | 60 | | | |
| f⊤ | Current-Gain—Bandwidth Product | I _C = -0.5A;V _{CE} = -10V;f _{test} = 1MHz | | 5 | | MHz |

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